

Comment on “Density of States of Disordered Two-Dimensional Crystals with Half-Filled Band”

In a recent letter [1] Nakhmedov et al. (NKO) claimed that the Van Hove singularity at $\epsilon = 0$ in the density of states (DoS) $\rho(\epsilon)$ of the two-dimensional crystal with half-filled tight-binding band survives the addition of substitutional impurities. The authors found a singular average DoS as ($\epsilon \rightarrow 0$) (Eq. (14) in Ref. [1]):

$$\rho(\epsilon) \propto (2\pi\epsilon_F\tau_\pi)^{1/2} \ln^{1/2} \left(\frac{1}{4\tau_\pi|\epsilon|} \right), \quad (1)$$

where ϵ_F is the Fermi energy and τ_π is the electronic relaxation time due to elastic processes where incoming and outgoing momenta differ by a nesting wave vector $\mathbf{P}_0 = (\pi, \pi)$. This result is very counter-intuitive. Naively, one would expect that the potential disorder simply broadens local energy levels and washes out any singularities in the DoS. In this comment we show that the DoS is indeed non-singular. The derivation in Ref. [1] suffers from several inconsistencies. We proceed by correcting them one by one, and find a finite DoS at half filling.

First, the authors used the standard impurity averaged perturbation theory, and calculated the weak localization correction to the DoS. This correction was added to the DoS $\rho_0^{(2)}(\epsilon)$ of the pure crystal. This is inconsistent with the standard scheme that the authors use [2] in which one starts with the self-consistent Born approximation for Green’s functions and the DoS:

$$\rho_B(\epsilon) = -\frac{2}{\pi} \text{Im} \int \frac{d^2p}{(2\pi)^2} G_R^0(\mathbf{p}, \epsilon), \quad (2)$$

where $G_R^0(\mathbf{p}, \epsilon) = \{\epsilon - [\epsilon(\mathbf{p}) - \epsilon_F] + \frac{i}{2\tau}\}^{-1}$ is the retarded Green’s function. Evaluating this integral for energies smaller than $1/\tau$ we obtain a non-singular DoS, since in this case the Van Hove singularity is cut off by the scattering rate:

$$\rho_B(0) = \frac{2}{(\pi a)^2 \epsilon_F} \ln(\epsilon_F \tau). \quad (3)$$

Next, we consider the $1/(\epsilon_F \tau)$ correction to this DoS. In Ref. [1] it was found to be singular. In their analysis the authors separated the scattering processes into two classes — with momentum transfers close to 0 and the nesting vector $\mathbf{P}_0$. The scattering with nesting was assumed to be dominant, and the corresponding scattering times, τ_0 and τ_π , very different: $\tau_\pi \ll \tau_0$. This statement does not agree with the expressions for these times given in Ref. [1]:

$$\begin{aligned} \frac{1}{\tau_0} &= \frac{C_{\text{imp}}}{(2\pi)^2} \int \frac{d\mathbf{S}}{|\mathbf{V}_{\mathbf{k}}|} |U(\mathbf{k}, 0)|^2, \\ \frac{1}{\tau_\pi} &= \frac{C_{\text{imp}}}{(2\pi)^2} \int \frac{d\mathbf{S}}{|\mathbf{V}_{\mathbf{k}}|} |U(\mathbf{k}, \mathbf{P}_0)|^2, \end{aligned}$$

where C_{imp} is the concentration of impurities, $d\mathbf{S}/|\mathbf{V}_{\mathbf{k}}|$ is the usual Fermi surface measure, and $U(\mathbf{k}, \mathbf{q})$ is the scattering matrix element for momentum transfer $\mathbf{q}$. For example, in the case of point-like impurities ($U(\mathbf{k}, \mathbf{q}) = \text{const}$) one finds $\tau_\pi = \tau_0$, while for reasonable finite size impurities these times are of the same order of magnitude. However, from purely formal point of view one still can consider the model with $\tau_\pi \ll \tau_0$.

Finally, the weak localization correction to the DoS is expressed in terms of the quantity $\alpha(\epsilon)$, see Eqs. (9,10) in Ref. [1], which involves integrals of Cooperons and diffusons, Eqs. (5,6) of Ref. [1]. Evaluating these integrals, NKO cut off the leading logarithmic contribution at $kl \sim \sqrt{\epsilon\tau}$. This is correct for energies in the range $\epsilon\tau_0 > 1$. However, when $\epsilon \rightarrow 0$, the logarithm is cut off by any finite τ_0 , since then $1 - (\tau/\tau_\pi)^2$ in the denominators of NKO’s Eqs. (5,6) is small but finite. Therefore, the quantity $\alpha_0(\epsilon)$ saturates as $\epsilon \rightarrow 0$ at the finite value

$$\alpha_0(0) = \frac{1}{2\pi\epsilon_F\tau_\pi} \ln \frac{\tau_0}{\tau_\pi}. \quad (4)$$

Since the expansion parameter $1/\epsilon_F\tau_\pi \ll 1$, the weak localization correction is also small, $\alpha_0(0) \ll 1$, and does not essentially modify the DoS $\rho_B(0)$. The value $\alpha_0(0) \sim 1$ is only achieved for $\tau_0/\tau_\pi \sim \exp(2\pi\epsilon_F\tau_\pi)$. Such extremely large value cannot be obtained for a generic disorder potential.

Combining our Eqs. (3,4) with Eq. (12) in Ref. [1], we arrive at

$$\rho(0) = \frac{2}{(\pi a)^2 \epsilon_F} \frac{\ln(\epsilon_F \tau)}{\sqrt{1 + \alpha_0(0)}}, \quad (5)$$

a finite result.

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